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Published in:
Technical Digest of the 18th IEEE Conference on Micro Electro Mechanical Systems, MEMS 2005

Link to article, DOI:
10.1109/MEMSYS.2005.1453978

Publication date:
2005

Document Version
Publisher's PDF, also known as Version of record

Citation (APA):

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FLEXIBLE STAMP FOR NANOIMPRINT LITHOGRAPHY

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ABSTRACT

The design, fabrication and performance of a flexible silicon stamp for homogenous large area nanoimprint lithography (NIL) are presented. The flexible stamp is fabricated by bulk semiconductor micro machining of a 4-inch silicon wafer and consists of thick anchor-like imprint areas connected by membranes. The bending stiffness difference between the imprint areas and the membranes ensures that the deformation of the stamp during the imprint process mainly takes place in the membranes, leaving the imprint structures unaffected. By this design the strong demand to the parallelism between stamp and substrate in the imprint situation is decoupled from the pressing tool and the wafer quality. The stamp consist of 1562 imprint areas (1 mm × 1 mm) containing the patterns to be replicated. The imprinted patterns are characterized with respect to the imprint depth and the polymer residual layer thickness. It is found that within a 50 nm diameter the polymer residual layer thickness is 18.8 nm with a standard deviation of 6.6 nm.

1. INTRODUCTION

Nanoimprint lithography (NIL) is a parallel process lithography technique capable of replicating nm to mm sized structures in a single parallel process step [1]. In thermal NIL a hard stamp, patterned with the structure to be replicated, is pressed into a thermoplast at a temperature above the glass transition temperature, \( T_g \), of the thermoplast. When the stamp is completely pressed into the thermoplast, cooling is initiated, and the stamp is separated from the thermoplast at a temperature below \( T_g \). Thereby the inverse stamp profile is replicated into the thermoplast, Fig. 1.

Parallel processing lithography techniques capable of patterning nm sized structures is of great interest for the volume manufacture of components containing nm sized features. The patterning of nm sized structures depend on expensive lithography techniques, e.g. electron beam lithography, x-ray lithography, and extreme ultra violet lithography. NIL is an obvious candidate for patterning of such structures, since only a master stamp has to be fabricated. The master stamp can then be replicated to stamp copies and these are used in the fabrication line [2]. In this way the cost of making components containing nm sized structures is reduced dramatically. The great potential of NIL to be a low cost lithography tool for sub-μm patterns is envisaged by the recent uptake of NIL on the International Technology Roadmap for Semiconductors (ITRS) [3], where NIL is appointed to be one of the potential lithography techniques to deliver the 32-nm node in 2013. However, in order to fulfill the demands from the ITRS to NIL there are some challenges to solve. The most important of these are: Homogeneous large area imprint, sub-μm to sub-μm aligning, error detection, fast imprint cycles and critical dimension control. The flexible silicon stamp presented here addresses the first of these challenges.

2. DESIGN

Considering large area thermal NIL a critical parameter is the thickness and variations of the polymer residual layer, i.e. the polymer film in the areas where the stamp protrusions have imprinted. Thick residual layers will cause pattern widen-
ing during removal, which is needed to get access to the substrate. Variations in the residual layer will cause an uneven patterning widening, i.e., loss of the critical dimensions during removal. The removal of the residual layer is often performed by oxygen plasma etching, see Fig. 1. Knowledge about the protrusion height, \( h_p \), the polymer thickness, \( h_0 \), and the variation of these \( \delta h_p \) and \( \delta h_0 \) is important. In a perfect stamp filling situation where stamp and substrate are parallel and without stamp bending, mass conservation of the polymer gives the expected polymer residual layer thickness:

\[
h_r = h_0 - h_p(1 - \nu),
\]

where \( \nu \) is the stamp protrusion coverage, i.e., the ratio between elevated and recessed area in the imprint areas. From Eq. 1 the expected variation of the polymer residual layer, \( \delta h_r \), is found to

\[
\delta h_r = \sqrt{\delta h_0^2 + (\nu \delta h_p)^2}
\]

Thereby it is important to control \( \delta h_0 \) and \( \delta h_p \) in order to achieve control of the polymer residual layer thickness. In addition to this the parallelism between the stamp and substrate is important. Taking the demand to the uniformity of the residual layer to be 5 nm variation over a 4-inch wafer, the challenge scales up to pressing two soccer fields together in a parallel manner with an accuracy of 5 \( \mu \)m. This is a tremendous task considering that the warp of a standard 4-inch wafer is approximately 5 \( \mu \)m. An obvious way to approach the challenge of parallelism is to consider micro electro mechanical systems (MEMS) technology and exploit the possibilities of control on the \( \mu \)m and nm scale that semiconductor processing offers. By using MEMS technology in the design of the stamp the demands to the parallelism between the stamp and substrate can be removed from the imprint tool and the wafer quality and into the stamp. In fact, no matter how parallel the pressing mechanism is in an imprint tool, the wafer warp and thickness variation still has to be considered. Using a structured silicon wafer as stamp and another silicon wafer as substrate the deformation of the wafers in order to achieve contact over the whole area is not controlled. Thereby there will be an uncontrolled pattern distortion of the imprinted pattern compared to the stamp which again results in loss of the critical dimensions. The flexible stamp presented here is designed to deform outside patterned areas and the patterns will be replicated without distortion.

The principle of the flexible stamp is to have imprint areas which are weakly coupled, ideally decoupled, from each other in the direction perpendicular to the wafer plane, but fixed in the wafer plane. This will cause the individual imprint areas to be able to adopt to any curvature of the substrate, and any defects from imprinting, e.g., particle contamination, will be localized to one or a few imprint areas, see Fig. 2. The fixation of the imprint areas in the wafer plane will prevent them from edging and ensure that they are imprinted parallel to the substrate.

This design principle described above is achieved by having many imprint areas which are placed on a membrane. The single imprint area consists of a mesa which is raised above the surface of the membrane, and is anchored through the membrane, Fig. 4E. The anchor has a thickness of the original silicon wafer, and the ratio between the thickness of the anchor and the thickness of the connecting membrane is 3.7, causing the bending stiffness of the imprint areas to be approximately 50 times larger than that of the membrane. The entire back side of the flexible stamp with the anchors are embedded in a mattress of poly-dimethylsiloxane (PDMS) to be able to apply a homogeneous pressure to the stamp. The silicon membrane and the back side PDMS mattress acts as a coupled spring system, with two springs in parallel. If the membrane is assumed to be a double clamped-clamped beam and the Young's modulus of silicon and PDMS to be 170 GPa and 750 kPa, respectively, the resulting spring constant for each imprint area is calculated to 1.85 \( \times 10^7 \) N/m.

In this demonstration of the flexible stamp, 1562 imprint areas are placed within a diameter of 70 mm on a 4-inch silicon wafer, and the supporting PDMS mattress has a diameter of 80 mm, see Fig. 3. All the imprint areas are 1 mm \( \times 1 \) mm and separated 0.5 mm. The imprint areas contain identical patterns, consisting of 8 lines (numbered 1 to 8), being 1 mm long and 25 \( \mu \)m wide. The stamp protrusion height, \( h_p \), is 283.0 nm with a standard deviation of 1.9 nm across the wafer. The lines are separated by 100 \( \mu \)m from each other, and the outer ones are placed 50 \( \mu \)m from the edge of the imprint area. The protrusion coverage in each imprint area is...
Figure 3: Overview of the imprint areas and the pattern within the areas. The 8 lines in 195 (dark) of the 1562 imprint areas have been characterized with respect to the polymer residual layer thickness. The support of the PDMS mattress on the back side has a diameter of 80 mm.

thereby 0.2. The reason for imprinting μm-sized patterns is twofold. First, the imprint process of large structures is challenging due to the large volume of polymer moved. Secondly, the 25 μm wide imprinted trenches allow for characterization of the polymer residual layer thickness.

3. FABRICATION

The flexible stamp is fabricated from a single side polished 4-inch silicon wafer. The fabrication process is outlined in Fig. 4. A 283 nm thick film of silicon dioxide is thermally grown on both sides of the wafer. The oxide is removed from the back side by BHF etch (Fig. 4 A). 1.5 μm thick photoresist (AZ5214e, Shipley) is spin-coated onto the back side and exposed (I-line UV-lithography) in a negative process to define the imprint areas and developed (AZ351B, Shipley). 300 nm of aluminium is e-beam evaporated on the back side (Alcatel SCM600) and a lift-off is performed using acetone and ultrasonic agitation. The aluminium on the back side is used as a hard etch mask in a deep reactive ion etch (RJE) (STS Cluster) which etches 1.7 μm into the silicon (Fig. 4 D). The photoresist is stripped and an anti-sticking film is deposited from a C₄F₈ plasma using the ASE [4]. Finally, the stamp is inserted into a mold for the PDMS mattress. The PDMS (Sylgard 184) is poured over the back side of the wafer and cured at 80°C for 2 hours in an oven (Fig. 4 E). A cross-sectional scanning electron micrograph of the completed flexible stamp is shown in Fig. 5.

Figure 4: Fabrication sequence for the flexible silicon stamp. The final flexible stamp is a hybrid between silicon and PDMS. All the silicon processing is performed by bulk silicon micro machining which is followed by molding of the PDMS mattress to the back side.

Figure 5: Scanning electron micrograph of the cross-section of the completed flexible stamp.

4. RESULTS

The flexible stamp is imprinted into a film of 50k poly-methylmethacrylate (PMMA) placed on a silicon substrate. The thickness of the PMMA film is 307 nm with a standard de-
viation of 4.9 nm. The stamp is imprinted into the PMMA by a homebuilt pressing tool. The imprint is performed in an evacuated environment having a pressure of 0.1 mbar, at a temperature of 170°C applying a force of 2000 N to the back side of the PDMS mattress. The imprint force is kept constant for 5 min before cooling is initiated. At a temperature of 70°C the imprint force is released and the stamp and substrate are manually separated.

Profilometer inspections show that the average imprint depth into the PMMA film is 249.4 nm with a standard deviation of 4.8 nm within the 50 mm diameter area, hence the stamp has not been completely filled during the imprint. Thereby the polymer residual layer thickness is determined by the parallelism between the stamp and substrate and the flow behavior of the polymer. The imprint is characterized with respect to the polymer residual layer thickness, \( h_r \), which is easily measured with a small spot size spectro-reflectometer (NanoSpec). Within a diameter of 50 mm the average polymer residual layer thickness is found to 18.8 nm with a standard deviation of 6.6 nm, see Fig. 6. Both the absolute residual layer thickness and the variation is on the same length scale as the radius of gyration, \( R_g \), which is 6.0 nm for 50k PMMA [6]. The radius of gyration is the characteristic length scale in a polymer network and for films in the order of a few \( R_g \) the polymer can no longer be considered fluid, but rather like a rigid material due to the entanglements of the polymer chains.

5. CONCLUSIONS
A flexible silicon stamp for thermal NIL is presented and the performance with respect to polymer residual layer thickness is characterized. The design of the flexible stamp is based on MEMS technology, whereby the demands to the parallelism between the stamp and substrate in the imprint situation are decoupled from the NIL pressing tools. The flexible stamp is designed to imprint homogeneously in a parallel manner over large areas, and it inherently imprints the imprint areas parallel to the substrate. A highly uniform polymer residual layer is obtained over a 50 mm diameter large area. The imprint is characterized with respect to the polymer residual layer thickness. The polymer residual layer thickness is found to 18.8 nm within the 50 mm diameter with a standard deviation of 6.6 nm. The polymer residual layer thickness is on the same length scale as the radius of gyration of the 50k PMMA. To our knowledge these results are state of the art within thermal NIL and comparable to the homogeneity results reported from UV-NIL [7, 8]. There are no identified obstacles in the fabrication of the flexible stamp that prevents it from being fabricated over larger areas.

ACKNOWLEDGEMENTS
The partial support of the EC-funded project NaPa (Contract no. NMP4-CT-2003-500120) is gratefully acknowledged. The contents of this work is the sole responsibility of the authors. One of the authors (R. H. Pedersen) gratefully acknowledges the financial support from the Oticon foundation.

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